

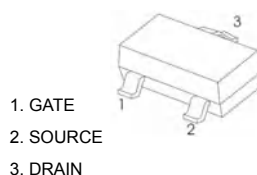
FEATURES

- High density cell design for low $R_{DS(ON)}$
- Voltage controlled small signal switch
- Rugged and reliable
- High saturation current capability

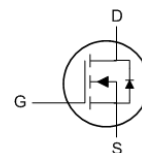
V_{DSS} 60 V
 I_D 3 A
 $R_{DS(ON)}$ 78 m Ω

S10

SOT-23



Equivalent Circuit



MAXIMUM RATINGS AND ELECTRICAL CHARACTERISTICS

Maximum ratings ($T_a=25^\circ\text{C}$ unless otherwise noted)

Parameter	Symbol	Value	Unit
Drain-Source Voltage	V_{DS}	60	V
Gate-Source Voltage	V_{GS}	± 20	V
Continuous Drain Current	I_D	3	A
Pulsed Drain Current (note 1)	I_{DM}	10	A
Power Dissipation	P_D	1.5	W
Thermal Resistance from Junction to Ambient (note 2)	$R_{\theta JA}$	357	$^\circ\text{C/W}$
Junction Temperature	T_J	150	$^\circ\text{C}$
Storage Temperature	T_{STG}	-55~+150	$^\circ\text{C}$

$T_a = 25^\circ\text{C}$ unless otherwise specified

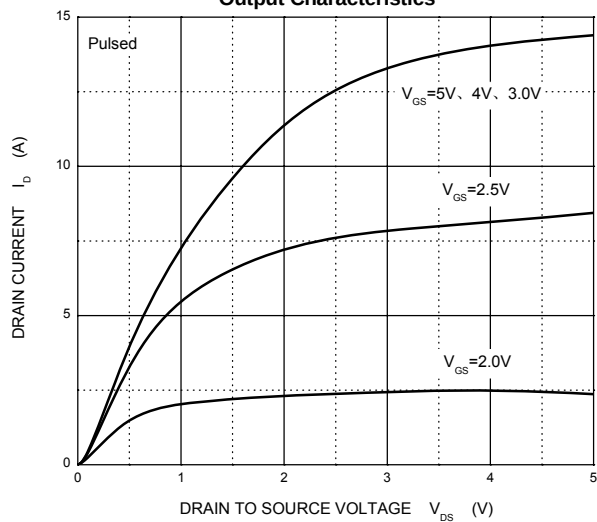
Parameter	Symbol	Test Condition	Min	Typ	Max	Unit
STATIC CHARACTERISTICS						
Drain-source breakdown voltage	V _{(BR)DSS}	V _{GS} = 0V, I _D =250μA	60			V
Zero gate voltage drain current	I _{DSS}	V _{DS} =60V,V _{GS} = 0V			1	μA
Gate-body leakage current	I _{GSS}	V _{GS} =±20V, V _{DS} = 0V			±100	nA
Gate threshold voltage (note 3)	V _{GS(th)}	V _{DS} =V _{GS} , I _D =250μA	1		2	V
Drain-source on-resistance (note 3)	R _{DS(on)}	V _{GS} =10V, I _D =3A		78	105	mΩ
		V _{GS} =4.5V, I _D =3A			125	mΩ
Forward tranconductance (note 3)	g _{FS}	V _{DS} =15V, I _D =2A	1.4			S
Diode forward voltage (note 3)	V _{SD}	I _S =3A, V _{GS} = 0V			1.2	V
DYNAMIC CHARACTERISTICS (note 4)						
Input Capacitance	C _{iss}	V _{DS} =30V,V _{GS} =0V,f =1MHz		247		pF
Output Capacitance	C _{oss}			34		pF
Reverse Transfer Capacitance	C _{rss}			19.5		pF
SWITCHING CHARACTERISTICS (note 4)						
Turn-on delay time	t _{d(on)}	V _{GS} =10V,V _{DD} =30V, I _D =1.5A,R _{GEN} =1Ω		6		ns
Turn-on rise time	t _r			15		ns
Turn-off delay time	t _{d(off)}			15		ns
Turn-off fall time	t _f			10		ns
Total Gate Charge	Q _g	V _{DS} =30V,V _{GS} =4.5V,I _D =3A		6		nC
Gate-Source Charge	Q _{gs}			1		nC
Gate-Drain Charge	Q _{gd}			1.3		nC

Notes :

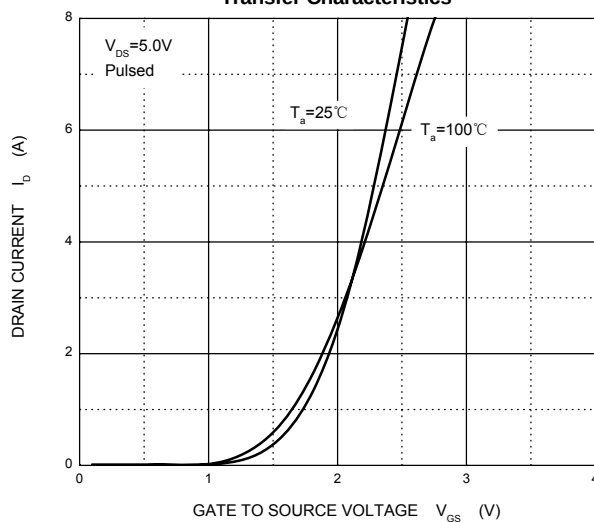
1. Repetitive rating : Pulse width limited by junction temperature.
2. Surface mounted on FR4 board , $t \leq 10s$.
3. Pulse Test : Pulse Width $\leq 300\mu s$, Duty Cycle $\leq 0.5\%$.
4. Guaranteed by design, not subject to producing.

RATING AND CHARACTERISTIC CURVES

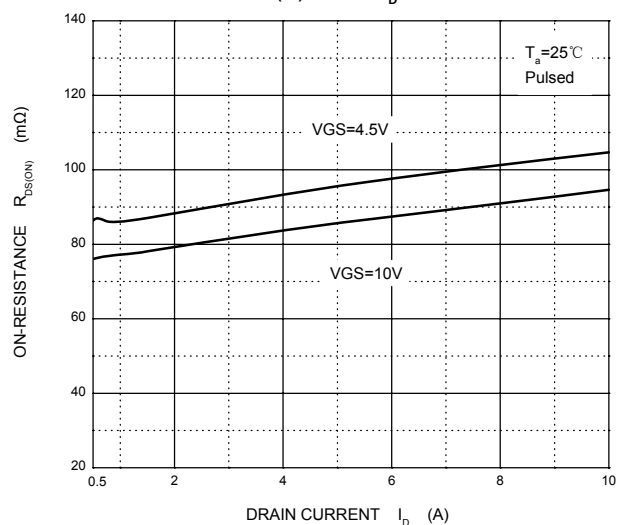
Output Characteristics



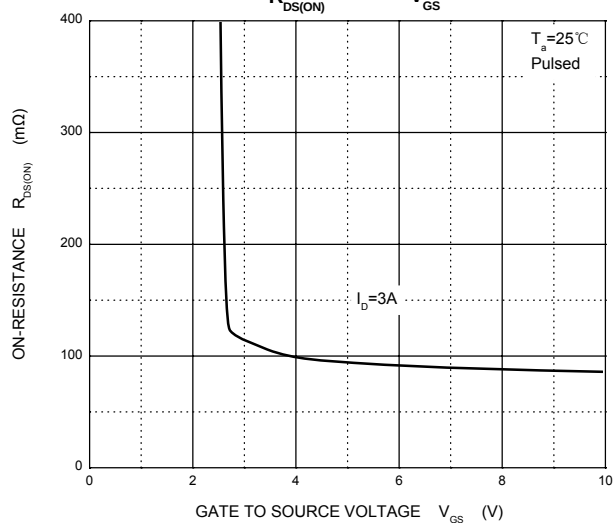
Transfer Characteristics



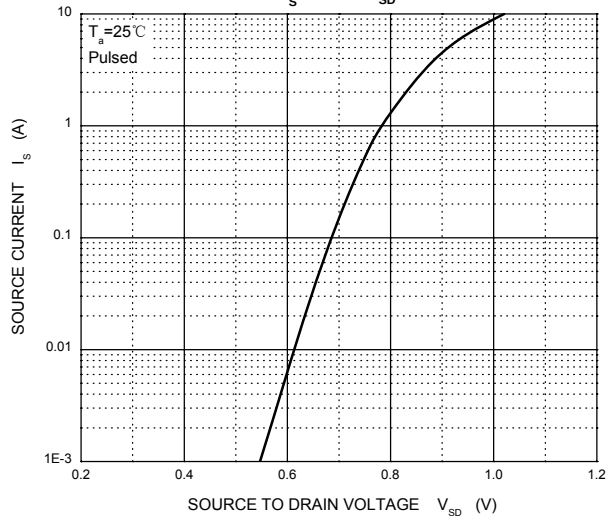
$R_{DS(ON)}$ — I_D



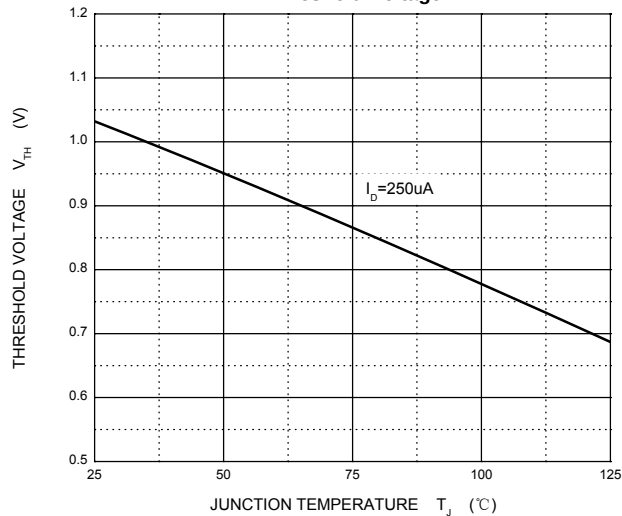
$R_{DS(ON)}$ — V_{GS}



I_S — V_{SD}

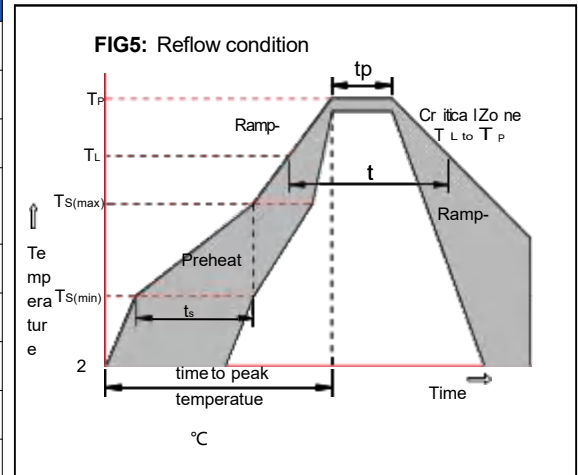


Threshold Voltage



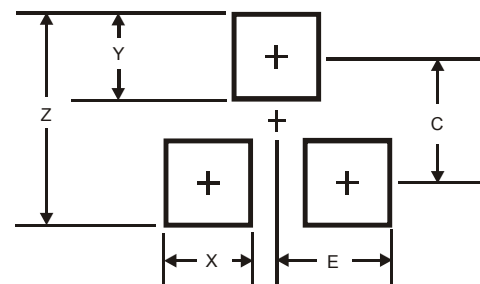
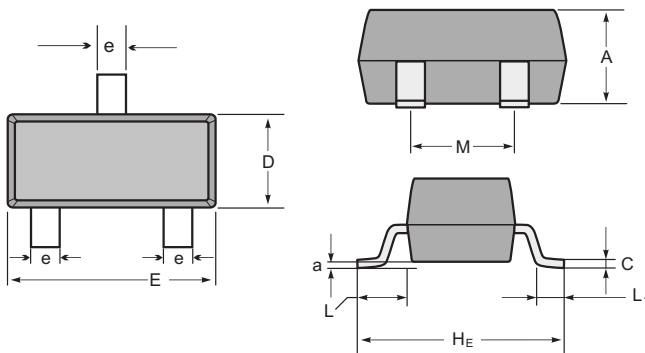
Soldering parameters

Reflow Condition		Pb-Free assembly (see as below)
Pre Heat	-Temperature Min ($T_{s(min)}$)	+150°C
	-Temperature Max($T_{s(max)}$)	+200°C
	-Time (Min to Max) (ts)	60-180 secs.
Average ramp up rate (Liquid us Temp (T_L) to peak)		3°C/sec. Max
$T_{s(max)}$ to T_L - Ramp-up Rate		3°C/sec. Max
Reflow	-Temperature(T_L)(Liquid us)	+217°C
	-Temperature(t_L)	60-150 secs.
Peak Temp (T_P)		+260(+0/-5)°C
Time within 5°C of actual Peak Temp (t_P)		30 secs. Max
Ramp-down Rate		6°C/sec. Max
Time 25°C to Peak Temp (T_P)		8 min. Max
Do not exceed		+260°C



Package Dimensions & Suggested Pad Layout

SOT23

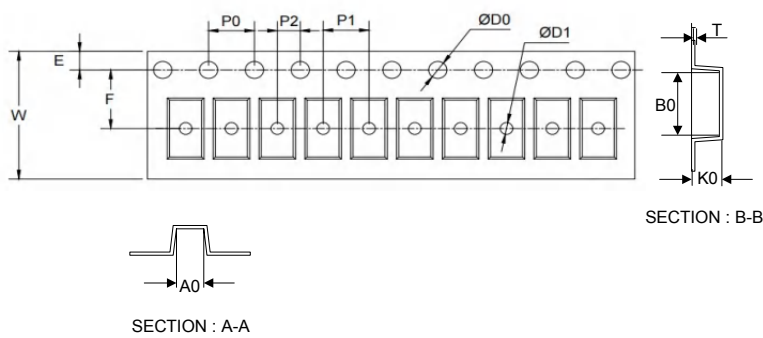
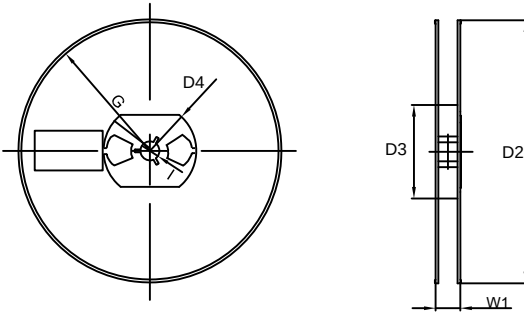


SOT-23 mechanical data

UNIT		A	C	D	E	H _E	e	M	L	L ₁	a
mm	max	1.1	0.15	1.4	3.0	2.6	0.5	1.95	0.55 (ref)	0.36 (ref)	0.0
	min	0.9	0.08	1.2	2.8	2.2	0.3	1.7			0.15
mil	max	43	6	55	118	102	20	77	22 (ref)	14 (ref)	0.0
	min	35	3	47	110	87	12	67			6

Dimensions	SOT23
Z	2.9
X	0.8
Y	0.9
C	2.0
E	1.35

Tape & reel specification

Tape		Symbol	Dimension (mm)
		P0	4.00±0.10
		P1	4.00±0.10
		P2	2.00±0.10
		D0	1.55±0.10
		D1	1.05±0.10
		E	1.55±0.10
		F	3.60±0.10
		W	8.00±0.10
		A0	3.80±0.20
		B0	3.25±0.20
		K0	1.45±0.10
		T	0.25±0.05
		D2	178.0±3.0
		D3	55Min.
		D4	R24.0±3.0
7" Reel		G	R82.0±3.0
		I	13.0±2.0
		W1	11.0±3.0
		Quantity: 3000PCS	